

\*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form PTO-1449			Docket No: 112	Docket No: 112028-0014		Serial No. 09/033,997		
INFORMATION-DISCENSIVE STATEMENT			Applicant: Mar	Applicant: Maria E. Barone et al.				
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